

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((deep\$1react\$3 near1 ion\$2) or (deep near1 react\$3 near1 ion\$2) or (drie)) with recise	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 08:34
L2	44	((deep\$1react\$3 near1 ion\$2) or (deep near1 react\$3 near1 ion\$2) or (drie)) with precise	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 08:34
S1	1	(deep near1 reative near1 ion near1 etching)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:15
S2	1393	(deep near1 reactive near1 ion near1 etching)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:15
S3	117	(deep near1 reactive near1 ion near1 etching) with anisotropic near6 etching	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:27
S4	2	"5434939".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:19
S5	29	("5434939").URPN.	USPAT	OR	OFF	2005/10/20 08:20
S6	9	(deep near1 reactive near1 ion near1 etching) with anisotropic near6 etching near10 (EPW or (ethylene or diamine or pyrocatechol))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:24
S7	9	(deep near1 reactive near1 ion near1 etching) with anisotropic near6 etching with (EPW or (ethylene\$1diamine near2 pyrocatechol))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:24
S8	10	(deep near1 reactive near1 ion near1 etching) same anisotropic near6 etching with (EPW or (ethylene\$1diamine near2 pyrocatechol))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:27

S9	1	S8 not S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:26
S10	2	"5501893".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:26
S11	5	(deep near1 reactive near1 etching) same (anisotropic near6 etching) with (EPW or (ethylene\$1diamine near2 pyrocatechol))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:28
S12	5	(deep near1 reactive near1 etching) same (anisotropic near6 etching) same (EPW or (ethylene\$1diamine near2 pyrocatechol))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:28
S15	5	(deep near1 reactive near1 etching) same (anisotropic near6 etching) same (EPW or (ethylene\$1diamine near2 pyrocatechol))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:29
S16	16	(deep near1 reactive near1 etching) same (anisotropic near6 etching)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:30
S17	2	mask\$3 same (deep near1 reactive near1 etching) and (anisotropic near6 etching) and (fiber or fibre or waveguide) with optic\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:31
S18	15	mask\$3 same (deep near1 reactive near1 etching) and (anisotropic near6 etching)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:31
S19	5200	mask\$3 same (ion near5 etching) and (anisotropic near6 etching)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 08:32
S20	667	mask\$3 same (ion near5 etching) and (anisotropic near6 etching) and (fiber or fibre or waveguide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:32

S21	510	mask\$3 same (reactive near5 ion near5 etching) and (anisotropic near6 etching) and (fiber or fibre or waveguide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:32
S22	6	mask\$3 same (deep\$1reactive near5 ion near5 etching) and (anisotropic near6 etching) and (fiber or fibre or waveguide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:33
S23	87	mask\$3 same (drie) and (anisotropic near6 etching) and (fiber or fibre or waveguide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:33
S24	29	mask\$3 same (drie) and (anisotropic near6 etching) and (fiber or fibre or waveguide)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:34
S25	13	mask\$3 same (drie) same (anisotropic near6 etching) and (fiber or fibre or waveguide)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:36
S26	2	mask\$3 same (drie) same (anisotropic near6 etching with (edp))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:36
S27	3	(drie) same (anisotropic near6 etching with (edp))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:37
S28	40	(drie) same (anisotropic near6 etching with (wet or solution or solvent))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:39
S29	74	(drie) and (anisotropic near6 etching same (wet or solution or solvent))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 08:39
S30	34	S29 not S28	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:02
S33	2	"5434939".pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:03
S34	1	"06138341"	JPO	OR	ON	2005/10/20 10:16

S38	51	drie near1 etching same precis\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:17
S39	22	drie near1 etching same precis\$4	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:18
S40	25	drie near1 etching same advantag\$5	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:19
S41	21	S40 not S39	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:18
S42	22	drie near3 etching same precis\$4	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:20
S43	30	drie with etching same precis\$4	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:20
S44	8	S43 not S42	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:22
S45	2	"5876187".pn.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:22
S46	1	S45 and etching	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:23
S47	38445	drie	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:23

S48	420	drie with etching	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:26
S49	28	S48 and @pd<"19990601"	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:25
S50	5	S49 and (precis\$3 or better)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:24
S51	11	((deep\$1react\$3 near1 ion\$2) with etching	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:27
S52	936	((deep\$1react\$3 near1 ion\$2) or (deep near1 react\$3 near1 ion\$2) or (drie)) same etching	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:32
S53	386	S52 and (precis\$3)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:32
S54	22	S53 and @pd<"19990101"	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:29
S55	30	S53 and @pd<"20000101"	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:29
S56	18370	((deep\$1react\$3 near1 ion\$2) or (deep near1 react\$3 near1 ion\$2) or (drie) or rie) same etching	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:34
S57	17434	S56 not S52	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:32

S58	4235	S57 and (precis\$3)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:32
S59	98	S58 and (edp)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:33
S60	1	((deep\$1react\$3 near1 ion\$2) or (deep near1 react\$3 near1 ion\$2) or (drie) or rie) same etching same precis\$3 same edp	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:34
S61	54	((deep\$1react\$3 near1 ion\$2) or (deep near1 react\$3 near1 ion\$2) or (drie) or rie)) same etching same precis\$3 same ((wet\$1etching or (wet near1 etching))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:47
S62	788	((deep\$1react\$3 near1 ion\$2) or (deep near1 react\$3 near1 ion\$2) or (drie)) with ((react\$4 near1 ion\$3) or rie)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 08:33
S63	44	S62 and @pd<"20000101"	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:55